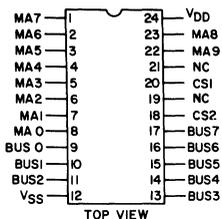


# CDP1834, CDP1834C



NC = NO CONNECTION  
92CS-28727  
**TERMINAL ASSIGNMENT**

## 1028-Word x 8-Bit Static Read-Only Memory

**Features:**

- Industry pin compatible
- Three-state outputs

The RCA-CDP1834 and CDP1834C are 8192-bit mask-programmable CMOS read-only memories organized as 1024-words x 8-bits and designed for use in CDP1800-series microprocessor systems. The CDP1834-series ROM's are completely static; no clocks are required

Two Chip-Select inputs (CS1, CS2) are provided for memory expansion. The polarity of each Chip-Select is user mask-

programmable. The CDP1834-series is pin-compatible with industry type 2708 EPROM. The CDP1834C is functionally identical to the CDP1834. The CDP1834 has a recommended operating voltage range of 4 to 10.5 volts and the CDP1834C has a recommended operating voltage range of 4 to 6.5 volts. The CDP1834 and the CDP1834C are supplied in 24-lead dual-in-line ceramic packages (D suffix) and in 24-lead dual-in-line plastic packages (E suffix). The CDP1834C is also available in chip form (H suffix).

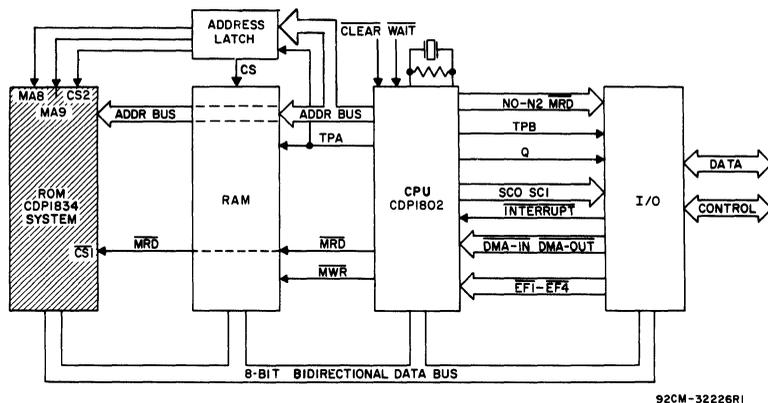


Fig 1 - Typical CDP1802 microprocessor system.

# CDP1834, CDP1834C

**MAXIMUM RATINGS, Absolute-Maximum Values:**

DC SUPPLY-VOLTAGE RANGE, (V<sub>DD</sub>):

(All voltage values referenced to V<sub>SS</sub> terminal)

CDP1834	0.5 to +11 V
CDP1834C	-0.5 to +7 V

INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5 to V<sub>DD</sub> +0.5 V

DC INPUT CURRENT, ANY ONE INPUT ..... ±10 mA

POWER DISSIPATION PER PACKAGE (P<sub>D</sub>):

For T <sub>A</sub> = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T <sub>A</sub> = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 12 mW/°C to 200 mW
For T <sub>A</sub> = -55 to +100° C (PACKAGE TYPE D)	500 mW
For T <sub>A</sub> = 100 to +125° C (PACKAGE TYPE D)	Derate Linearly at 12 mW/°C to 200 mW

DEVICE DISSIPATION PER OUTPUT TRANSISTOR

For T<sub>A</sub> = FULL PACKAGE-TEMPERATURE RANGE ..... 100 mW

OPERATING-TEMPERATURE RANGE (T<sub>A</sub>):

PACKAGE TYPE D	-55 to +125° C
PACKAGE TYPE E	-40 to +85° C

STORAGE TEMPERATURE RANGE (T<sub>stg</sub>) ..... -65 to +150° C

LEAD TEMPERATURE (DURING SOLDERING):

At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10 s max. .... +265° C

**STATIC ELECTRICAL CHARACTERISTICS** at T<sub>A</sub> = -40 to +85° C, V<sub>DD</sub> 5%, Except as noted

CHARACTERISTIC		CONDITIONS			LIMITS						UNITS
		V <sub>O</sub> (V)	V <sub>IN</sub> (V)	V <sub>DD</sub> (V)	CDP1834			CDP1834C			
					Min.	Typ.*	Max.	Min.	Typ.*	Max.	
Quiescent Device Current	I <sub>DD</sub>	—	5	5	—	0.01	50	—	0.02	200	μA
		—	10	10	—	1	200	—	—	—	
Output Low Drive (Sink) Current	I <sub>OL</sub>	0.4	0, 5	5	0.8	—	—	0.8	—	—	mA
		0.5	0, 10	10	1.8	—	—	—	—	—	
Output High Drive (Source) Current	I <sub>OH</sub>	4.6	0, 5	5	-0.8	—	—	-0.8	—	—	mA
		9.5	0, 10	10	-1.8	—	—	—	—	—	
Output Voltage Low-Level	V <sub>OL</sub>	—	0, 5	5	—	0	0.1	—	0	0.1	V
		—	0, 10	10	—	0	0.1	—	—	—	
Output Voltage High Level	V <sub>OH</sub>	—	0, 5	5	4.9	5	—	4.9	5	—	V
		—	0, 10	10	9.9	10	—	—	—	—	
Input Low Voltage	V <sub>IL</sub>	0.5, 4.5	—	5	—	—	1.5	—	—	1.5	V
		1, 9	—	10	—	—	3	—	—	—	
Input High Voltage	V <sub>IH</sub>	0.5, 4.5	—	5	3.5	—	—	3.5	—	—	V
		1, 9	—	10	7	—	—	—	—	—	
Input Leakage Current	I <sub>IN</sub>	Any	0, 5	5	—	—	±1	—	—	±1	μA
		Input	0, 10	10	—	—	±2	—	—	—	
3-State Output Leakage Current	I <sub>OUT</sub>	0, 5	5	5	—	—	±1	—	—	±1	μA
		0, 10	10	10	—	—	±2	—	—	—	
Input Capacitance	C <sub>IN</sub>	—	—	—	—	5	7.5	—	5	7.5	pF
Output Capacitance	C <sub>OUT</sub>	—	—	—	—	10	15	—	10	15	pF
Operating Device Current	I <sub>DD1</sub> †	—	0, 5	5	—	7	10	—	7	10	mA
		—	0, 10	10	—	14	20	—	—	—	

\*Typical values are for T<sub>A</sub> = 25° C and nominal V<sub>DD</sub>.

†Outputs open-circuited; cycle time = 2.5 μs.

# CDP1834, CDP1834C

**OPERATING CONDITIONS** at  $T_A$  = Full Package Temperature Range. For maximum reliability, operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS				UNITS
	CDP1834		CDP1834C		
	Min.	Max.	Min.	Max.	
DC Operating Voltage Range	4	10.5	4	6.5	V
Input Voltage Range	$V_{SS}$	$V_{DD}$	$V_{SS}$	$V_{DD}$	

**DYNAMIC ELECTRICAL CHARACTERISTICS** at  $T_A = -40$  to  $+85^\circ\text{C}$ ,  $V_{DD} \pm 5\%$ , Input  $t_r, t_f = 10$  ns,  $C_L = 50$  pF,  $R_L = 200$  k $\Omega$

CHARACTERISTIC	TEST CONDITIONS $V_{DD}$ (V)	LIMITS						UNITS
		CDP1834			CDP1834C			
		Min.	Typ.*	Max.	Min.	Typ.*	Max.	
Access Time from Address Change, $t_{AA}$	5	—	575	750	—	575	750	ns
	10	—	350	425	—	—	—	
Access Time from Chip Select, $t_{ACS}$	5	—	600	700	—	600	700	ns
	10	—	325	410	—	—	—	
Chip Select Delay, $t_{CS}$	5	—	480	580	—	480	580	ns
	10	—	250	340	—	—	—	

\*Typical values are for  $T_A = 25^\circ\text{C}$  and nominal  $V_{DD}$ .

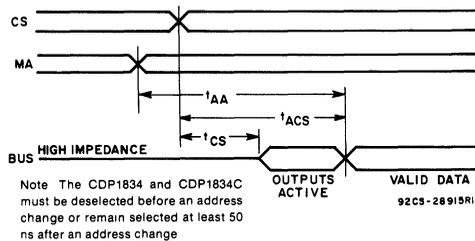


Fig. 2 - Timing waveforms.

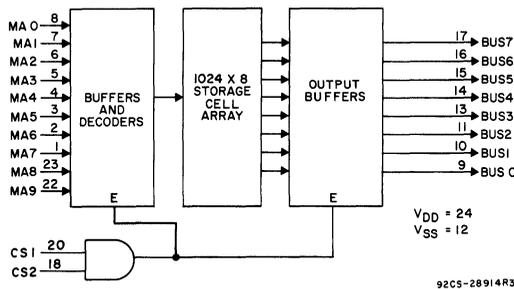


Fig. 3 - Functional diagram.